



Shantou Huashan Electronic Devices Co.,Ltd.

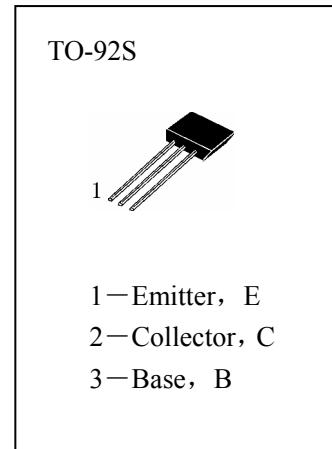
PNP SILICON TRANSISTOR

**HA114E**

■ SWITCHING CIRCUIT, INVERTER,  
INTERFACE CIRCUIT, DRIVER CIRCUIT

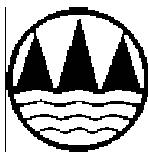
■ ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

$T_{\text{stg}}$ —Storage Temperature..... -55~150°C  
 $T_j$ —Junction Temperature..... 150°C  
 $P_C$ —Collector Dissipation..... 300mW  
 $V_{\text{CBO}}$ —Collector-Base Voltage..... -50V  
 $V_{\text{CEO}}$ —Collector-Emitter Voltage..... -50V  
 $V_{\text{EBO}}$ —Emitter-Base Voltage..... -10V  
 $I_C$ —Collector Current..... -100mA



■ ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-50			V	$I_C=-10 \mu\text{A}, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	-50			V	$I_C=-0.1\text{mA}, I_B=0$
ICBO	Collector Cut-off Current			-0. 1	$\mu\text{A}$	$V_{CB}=-40\text{V}, I_E=0$
ICEO	Collector Cut-off Current			-0. 5	$\mu\text{A}$	$V_{CE}=-40\text{V}, I_B=0$
IEBO	Emitter Cut-off Current	-195	-250	-360	$\mu\text{A}$	$V_{EB}=-5\text{V}, I_C=0$
HFE	DC Current Gain	30				$V_{CE}=-5\text{V}, I_C=-5\text{mA}$
VCE(sat)	Collector- Emitter Saturation Voltage		-0. 1	-0. 3	V	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$
VI (off)	Input Off Voltage	-0. 8	-1. 1	-1. 5	V	$V_{CE}=-5\text{V}, I_C=-0.1\text{mA}$
VI (on)	Input On Voltage	-1. 0	-2. 0	-4. 0	V	$V_{CE}=-0.2\text{V}, I_C=-10\text{mA}$
R1	Input Resistor	7. 0	10	13	Kohm	
R2/R1	Resistor Ratio	0. 8	1. 0	1. 2		
fT	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=-10\text{V}, I_C=-5\text{mA}$



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## ●Electrical characteristic curves

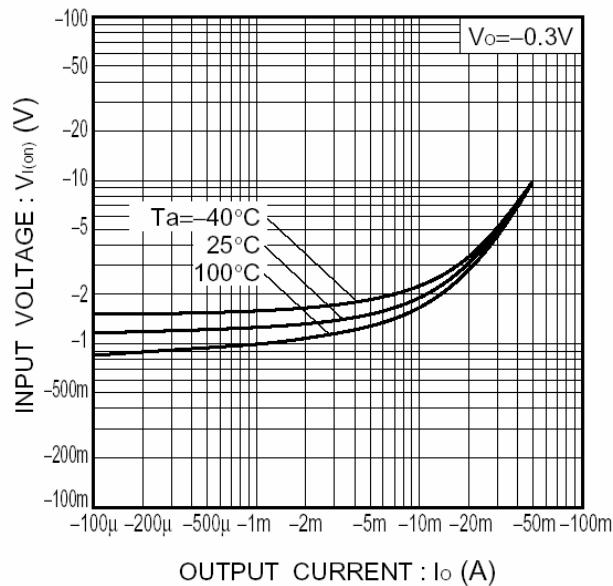


Fig.1 Input voltage vs. output current  
(ON characteristics)

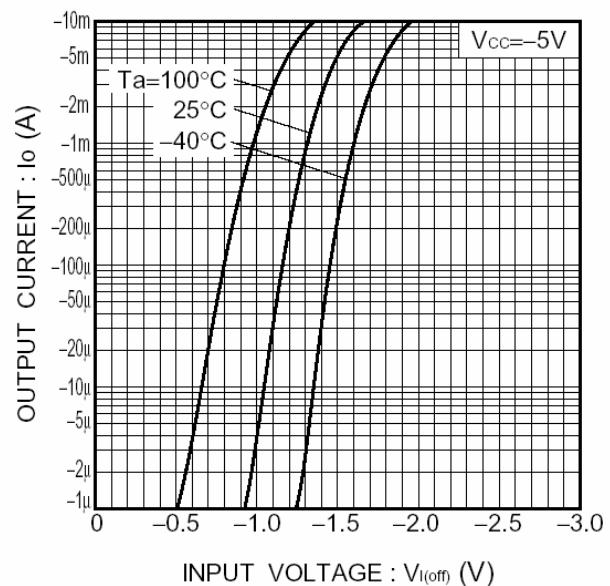


Fig.2 Output current vs. input voltage  
(OFF characteristics)

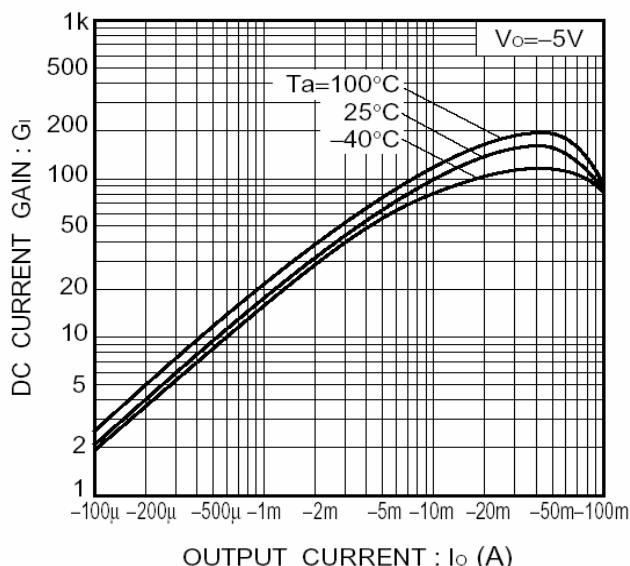


Fig.3 DC current gain vs. output current

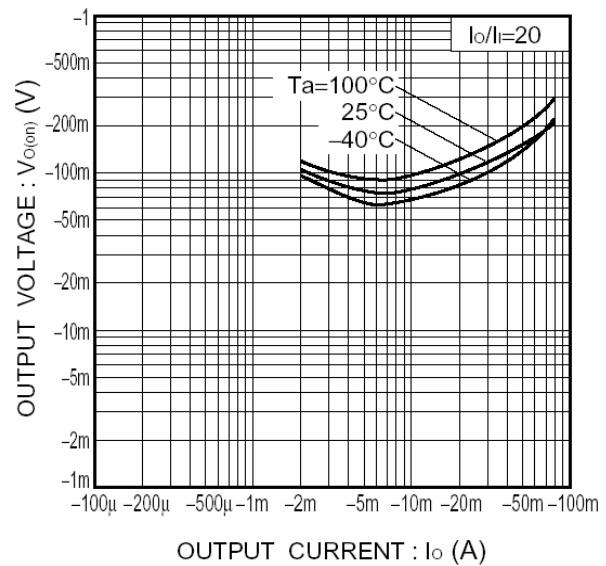


Fig.4 Output voltage vs. output current